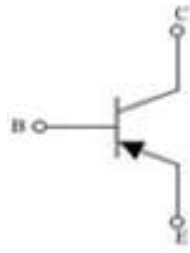
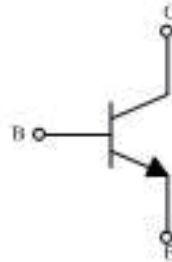


PNP/NPN Epitaxial Planar Transistors

(Pb) Lead(Pb)-Free

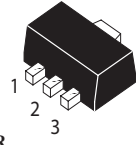


WTM772



WTM882

SOT-89



1. BASE
2. COLLECTOR
3. EMITTER

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Rating	Symbol	PNP/WTM772	NPN/WTM882	Unit
Collector-Emitter Voltage	V _{CEO}	-30	30	V _{dc}
Collector-Base Voltage	V _{CB0}	-40	40	V _{dc}
Emitter-Base Voltage	V _{EBO}	-5.0	6.0	V _{dc}
Collector Current (DC)	I _{C(DC)}	-3.0	3.0	A _{dc}
Total Device Dissipation T _A =25°C	P _D	0.5		W
Thermal Resistance, Junction to Ambient	R _{θJA}	250		°C/W
Junction Temperature	T _j	150		°C
Storage, Temperature	T _{stg}	-55 to +150		°C

Device Marking

WTM772=B772 , WTM882=D882

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min	Max	Unit
Collector-Emitter Breakdown Voltage (I _C = -10/10 mA _{dc} , I _B =0)	V _{(BR)CEO}	-30/30	-	V _{dc}
Collector-Base Breakdown Voltage (I _C = -100/100 uA _{dc} , I _E =0)	V _{(BR)CBO}	-40/40	-	V _{dc}
Emitter-Base Breakdown Voltage (I _E = -100/100 uA _{dc} , I _C =0)	V _{(BR)EBO}	-5.0/6.0	-	V _{dc}
Collector Cutoff Current (V _{CE} = -30/30 V _{dc} , I _B =0)	I _{CE0}	-	-10/10	uA _{dc}
Collector Cutoff Current (V _{CB} = -40/40 V _{dc} , I _E =0)	I _{CBO}	-	-1.0/1.0	uA _{dc}
Emitter Cutoff Current (V _{EB} = -6.0/6.0V _{dc} , I _C =0)	I _{EBO}	-	-1.0/1.0	uA _{dc}

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted) (Continued)

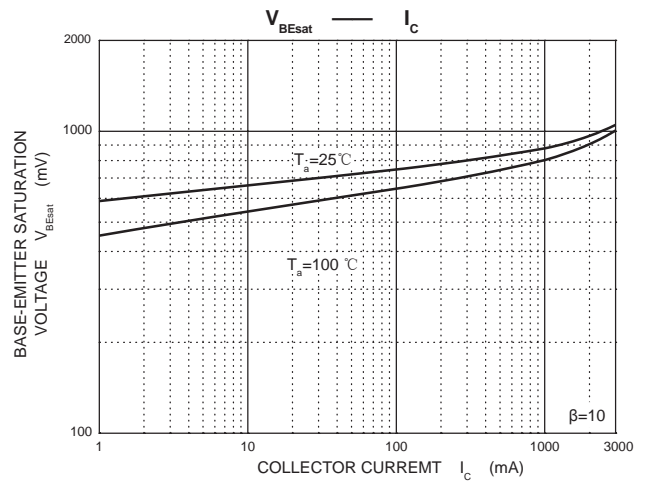
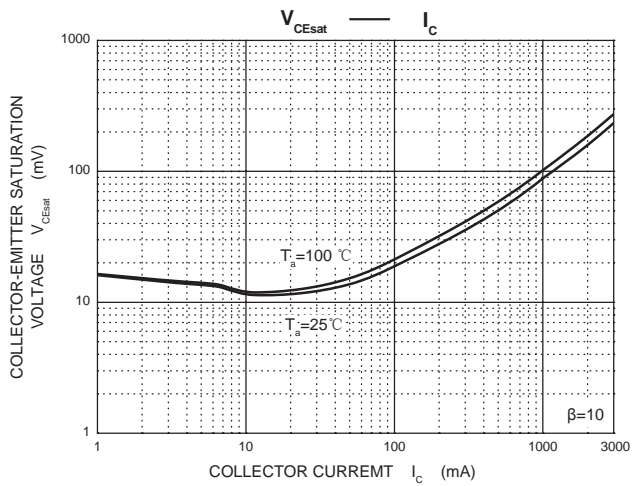
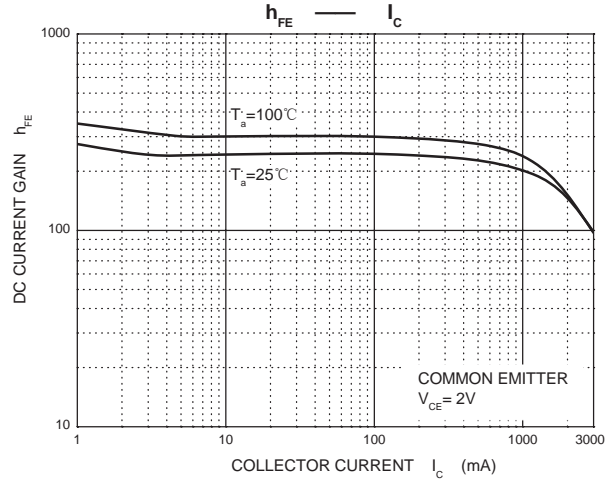
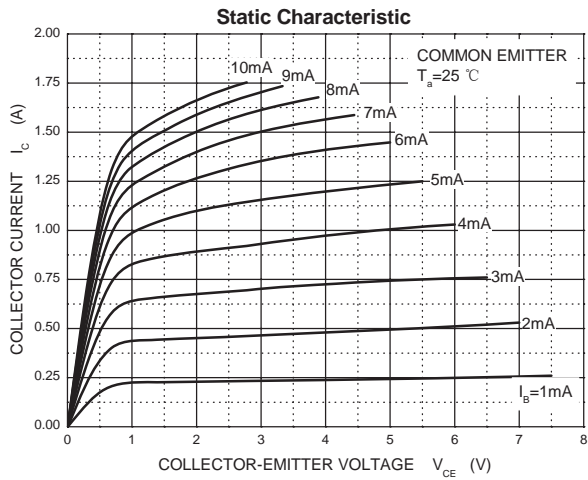
Characteristics	Symbol	Min	TYP	Max	Unit
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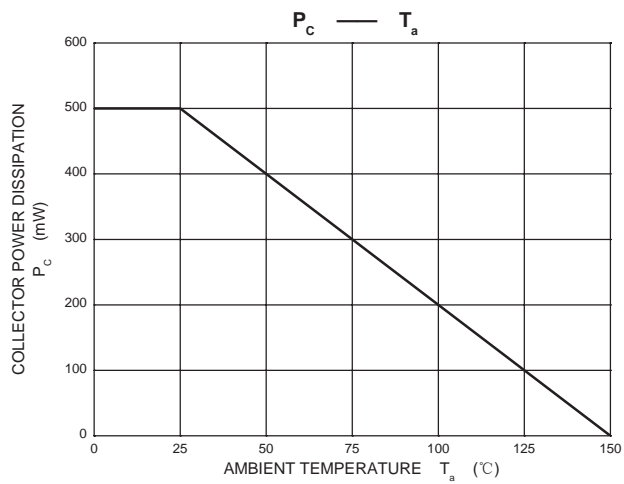
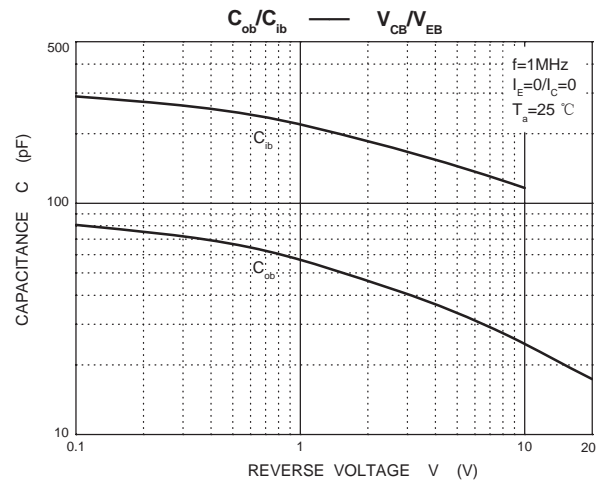
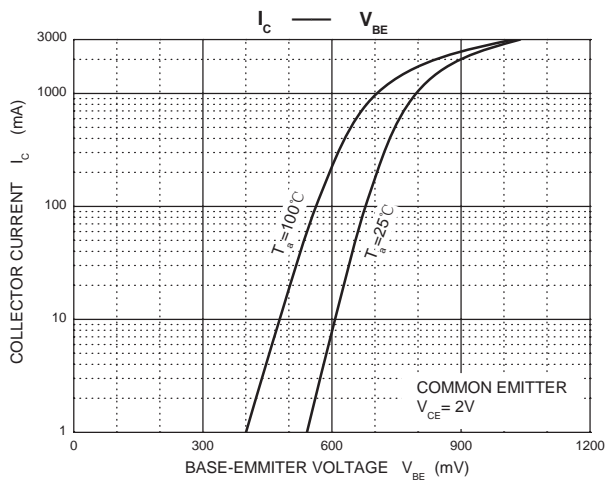
ON CHARACTERISTICS

DC Current Gain ($I_C = -1.0/1.0 \text{ Adc}, V_{CE} = -2.0/2.0 \text{ Vdc}$)	$h_{FE} (1)$	60/60	-	400/400	-
DC Current Gain ($I_C = -/100 \text{ mAdc}, V_{CE} = -/2.0 \text{ Vdc}$)	$h_{FE} (2)$	-/32	-	-	-
Collector-Emitter Saturation Voltage ($I_C = -2.0/2.0 \text{ Adc}, I_B = -0.2/0.2 \text{ Adc}$)	$V_{CE(sat)}$	-	-	-0.5/0.5	Vdc
Base-Emitter Saturation Voltage ($I_C = -2.0/2.0 \text{ Adc}, I_B = -0.2/0.2 \text{ Adc}$)	$V_{BE(sat)}$	-	-	-1.5/1.5	Vdc
Current-Gain-Bandwidth Product ($I_C = -0.1/0.1 \text{ Adc}, V_{CE} = -5.0/5.0 \text{ Vdc}, f = 10 \text{ MHz}$)	f_T	-	80/50	-	MHz

Classification of $h_{FE}(1)$

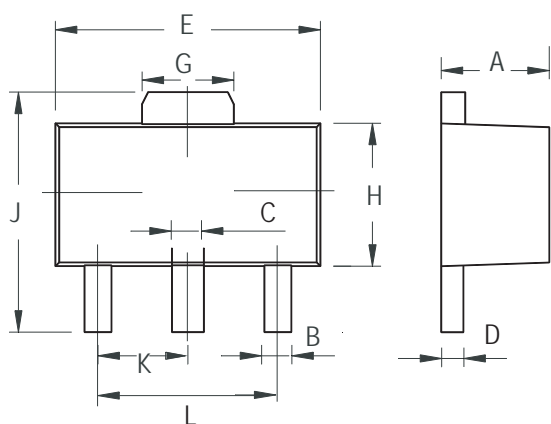
Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400





SOT-89 Outline Dimensions

unit:mm



SOT-89		
Dim	Min	Max
A	1.400	1.600
B	0.320	0.520
C	0.360	0.560
D	0.350	0.440
E	4.400	4.600
G	1.400	1.800
H	2.300	2.600
J	3.940	4.250
K	1.500TYP	
L	2.900	3.100